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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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# **N-Channel Power MOSFET**

600V, 4A, 0.9Ω

#### **FEATURES**

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance
- 100% UIL tested
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS			
PARAMETER VALUE UNIT			
$V_{DS}$	600	V	
R <sub>DS(on)</sub> (max)	0.9	Ω	
$Q_{q}$	9.6	nC	





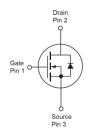


#### **APPLICATIONS**

- Power Supply
- Lighting







Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	600	V
Gate-Source Voltage		V <sub>GS</sub>	±30	V
Continuous Drain Current (Note 1)	T <sub>C</sub> = 25°C		4	А
	T <sub>C</sub> = 100°C	I <sub>D</sub>	2.4	А
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	12	Α
Total Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>DTOT</sub>	36.8	W
Single Pulsed Avalanche Energy (Not	e 3)	E <sub>AS</sub>	42.3	mJ
Single Pulsed Avalanche Current (No	te 3)	I <sub>AS</sub>	1.3	А
Operating Junction and Storage Ten	nperature Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	3.4	°C/W	
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>	62	°C/W	

**Thermal Performance Note:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air.

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ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2	3.3	4	V
Gate Body Leakage	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Drain-Source On-State Resistance (Note 4)	V <sub>GS</sub> = 10V, I <sub>D</sub> = 1.2A	R <sub>DS(on)</sub>		0.69	0.9	Ω
Dynamic (Note 5)					l	
Total Gate Charge	$V_{DS} = 380V, I_D = 4A,$ $V_{GS} = 10V$	Qg		9.6		
Gate-Source Charge		Q <sub>gs</sub>		2.0		nC
Gate-Drain Charge		$Q_{gd}$		4.5		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		315		
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		46.4		pF
Gate Resistance	F = 1MHz, open drain	$R_g$		3.2		Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 4A, V_{GS} = 10V,$	t <sub>d(on)</sub>		18		
Turn-On Rise Time		t <sub>r</sub>		10		
Turn-Off Delay Time		t <sub>d(off)</sub>		36.4		ns
Turn-Off Fall Time		t <sub>f</sub>		8		
Source-Drain Diode						
Forward Voltage (Note 4)	I <sub>S</sub> = 4A, V <sub>GS</sub> = 0V	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	V <sub>B</sub> = 100V, I <sub>S</sub> = 4A	t <sub>rr</sub>		185.5		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q <sub>rr</sub>		1.38		μC

#### Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L = 50mH,  $I_{AS} = 1.3A$ ,  $V_{DD} = 50V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$
- 4. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

#### **ORDERING INFORMATION**

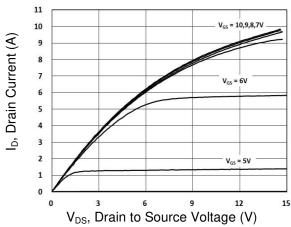
PART NO.	PACKAGE	PACKING
TSM60NB900CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

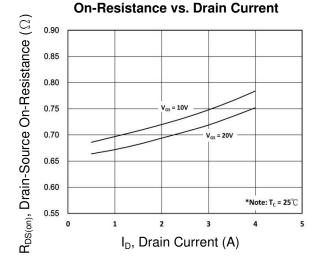


#### **CHARACTERISTICS CURVES**

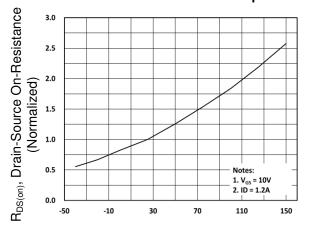
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

# **Output Characteristics**



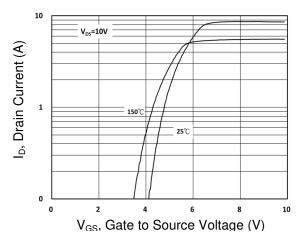


#### On-Resistance vs. Junction Temperature

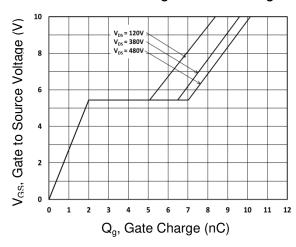


T<sub>J</sub>, Junction Temperature (°C)

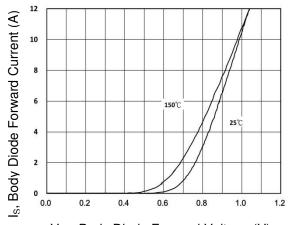
#### **Transfer Characteristics**



#### Gate-Source Voltage vs. Gate Charge



#### Source-Drain Diode Forward Current vs. Voltage



V<sub>SD</sub>, Body Diode Forward Voltage (V)

Version: A1608

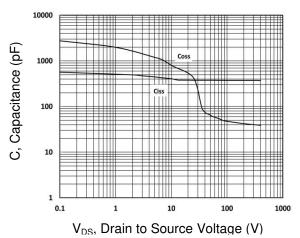
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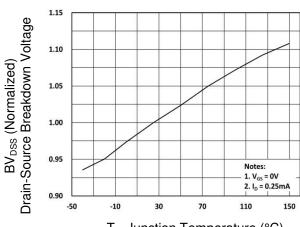
#### **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

### Capacitance vs. Drain-Source Voltage

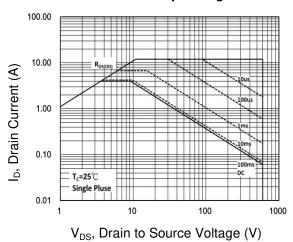


# BV<sub>DSS</sub> vs. Junction Temperature

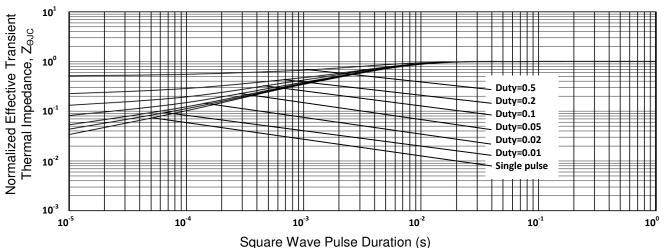


T<sub>.J</sub>, Junction Temperature (°C)

#### **Maximum Safe Operating Area**



#### Normalized Thermal Transient Impedance, Junction-to-Case





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# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TO-252 (DPAK)

6.60 ±0.20

0.53 ±0.05

1.07 ±0.10

1.07 ±0.10

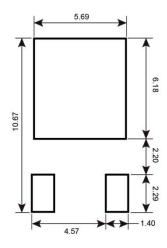
1.07 ±0.10

1.07 ±0.10

1.07 ±0.10

1.07 ±0.10

# SUGGESTED PAD LAYOUT (Unit: Millimeters)



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#### **MARKING DIAGRAM**



Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug W = Sep X = Oct Y = Nov Z = Dec

**L** = Lot Code (1~9, A~Z)



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